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Data Sheet

UV Enhanced Si Photodiode EOPD-950-0-1.2

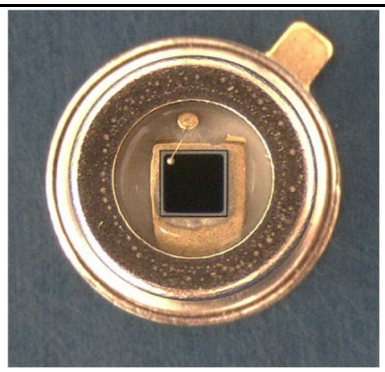
Rev. 02, 2020

Radiation	Type	Case
UV - near infrared	planar pn-Si photodiode	TO-46, glass window cap

The EOPD-950-0-1.2 is a 1.21 mm^2 active area Enhanced UV Sensitivity Photodiode in an isolated TO-46 can package. It is specifically designed for use @365 nm or Blue/Green applications requiring high signal and low noise.

FEATURES:
> Wide dynamic range
> High shunt resistance
> Ultra low noise

APPLICATIONS:
> Colorimeters
> Currency Authentication
> Spectroscopy equipment
> Fluorescence



RoHS COMPLIANT Pb-Free

Absolute Maximum Ratings

T_{amb}= 25°C, unless otherwise specified

Parameter	Test Conditions	Symbol	Value	Unit
Reverse voltage		V_R	50	V
Operating temperature range		T_{amb}	-40 to +110	°C
Storage temperature range		T_{stg}	-55 to +125	°C
Soldering temperature	max. 5 s, 3 mm from the body	T_{sld}	260	°C

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameters	Test conditions	Min	Typ	Max	Unit
Dark current	V_R= 5 V		0.2	1	nA
Forward voltage	I_F=2 mA			0.8	V
Breakdown voltage	I_R=10 µA	30			V
Spectral range		250		1100	nm
Peak sensitivity wavelength			950		nm
Responsivity	V_R=0 V, λ=365 nm	0.18	0.22		A/W
Responsivity	V_R=0 V, λ=633 nm		0.38		A/W
Shunt resistance	V_R=10 mV		800		MΩ
Junction capacitance	V_R=0 V, f=1 MHz		20		pF
Junction capacitance	V_R=5 V, f=1 MHz		6	8	pF
Response time	V_R=0 V, R_L=1 kΩ, λ_p=365 nm		100		ns

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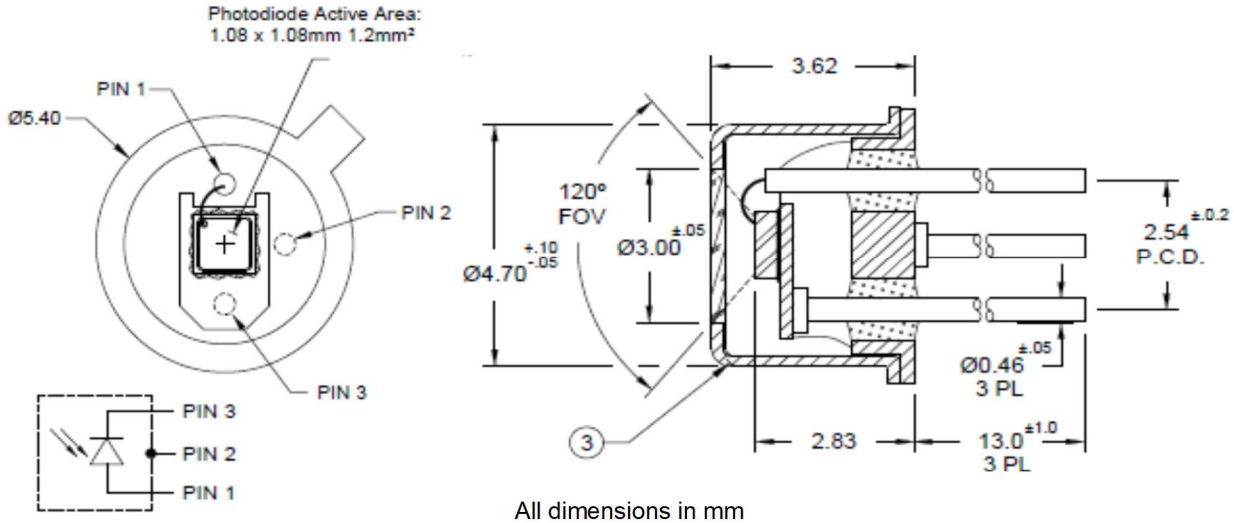
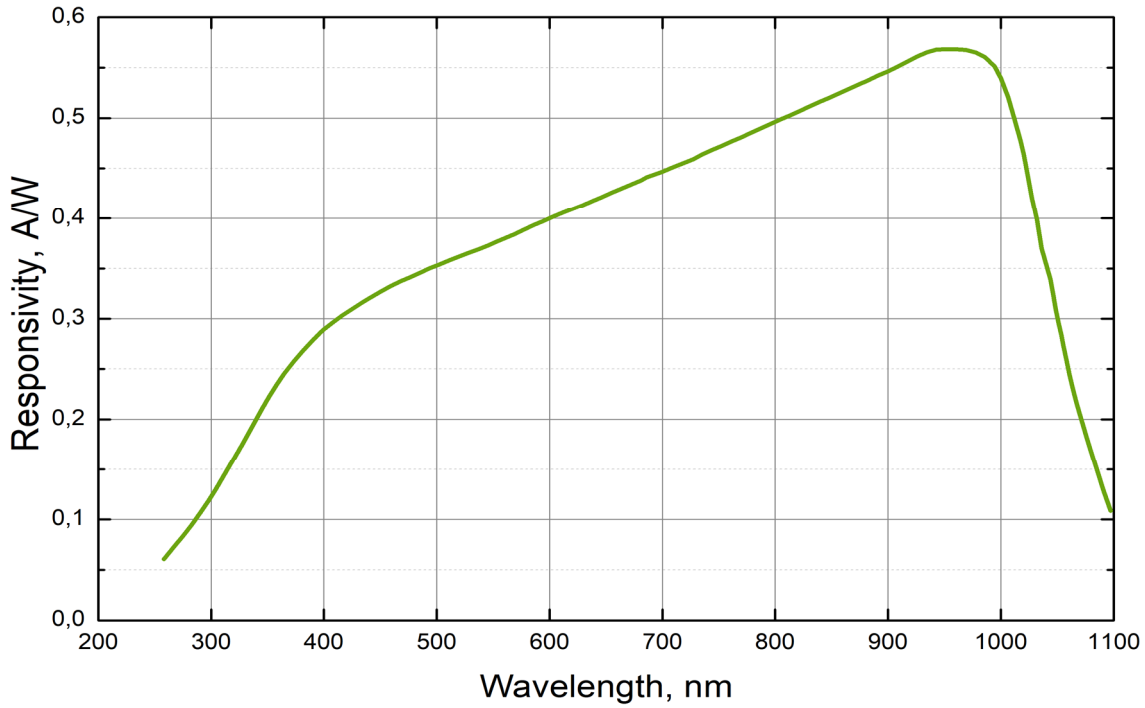


All dimensions in mm



Spectral sensitivity

Art. No. 143 160

RoHS COMPLIANT Pb Pb-Free